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Understanding **Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	264
Number of Logic Elements/Cells	2112
Total RAM Bits	75776
Number of I/O	206
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-2000he-6ftg256i

Features

■ Flexible Logic Architecture

- Six devices with 256 to 6864 LUT4s and 18 to 334 I/Os

■ Ultra Low Power Devices

- Advanced 65 nm low power process
- As low as 22 μ W standby power
- Programmable low swing differential I/Os
- Stand-by mode and other power saving options

■ Embedded and Distributed Memory

- Up to 240 kbits sysMEM™ Embedded Block RAM
- Up to 54 kbits Distributed RAM
- Dedicated FIFO control logic

■ On-Chip User Flash Memory

- Up to 256 kbits of User Flash Memory
- 100,000 write cycles
- Accessible through WISHBONE, SPI, I²C and JTAG interfaces
- Can be used as soft processor PROM or as Flash memory

■ Pre-Engineered Source Synchronous I/O

- DDR registers in I/O cells
- Dedicated gearing logic
- 7:1 Gearing for Display I/Os
- Generic DDR, DDRX2, DDRX4
- Dedicated DDR/DDR2/LPDDR memory with DQS support

■ High Performance, Flexible I/O Buffer

- Programmable sysIO™ buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8/1.5/1.2
 - LVTTTL
 - PCI
 - LVDS, Bus-LVDS, MLVDS, RSDS, LVPECL
 - SSTL 25/18
 - HSTL 18
 - Schmitt trigger inputs, up to 0.5 V hysteresis
- I/Os support hot socketing
- On-chip differential termination
- Programmable pull-up or pull-down mode

■ Flexible On-Chip Clocking

- Eight primary clocks
- Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
- Up to two analog PLLs per device with fractional-n frequency synthesis
 - Wide input frequency range (7 MHz to 400 MHz)

■ Non-volatile, Infinitely Reconfigurable

- Instant-on – powers up in microseconds
- Single-chip, secure solution
- Programmable through JTAG, SPI or I²C
- Supports background programming of non-volatile memory
- Optional dual boot with external SPI memory

■ TransFR™ Reconfiguration

- In-field logic update while system operates

■ Enhanced System Level Support

- On-chip hardened functions: SPI, I²C, timer/counter
- On-chip oscillator with 5.5% accuracy
- Unique TraceID for system tracking
- One Time Programmable (OTP) mode
- Single power supply with extended operating range
- IEEE Standard 1149.1 boundary scan
- IEEE 1532 compliant in-system programming

■ Broad Range of Package Options

- TQFP, WLCSP, ucBGA, csBGA, caBGA, ftBGA, fpBGA, QFN package options
- Small footprint package options
 - As small as 2.5 mm x 2.5 mm
- Density migration supported
- Advanced halogen-free packaging

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO2 family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks; these blocks are found in MachXO2-640/U and larger devices. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag “hard” control logic to minimize LUT usage.

The MachXO2 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO2 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks on MachXO2-640U, MachXO2-1200/U and larger devices. These blocks are located at the ends of the on-chip Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

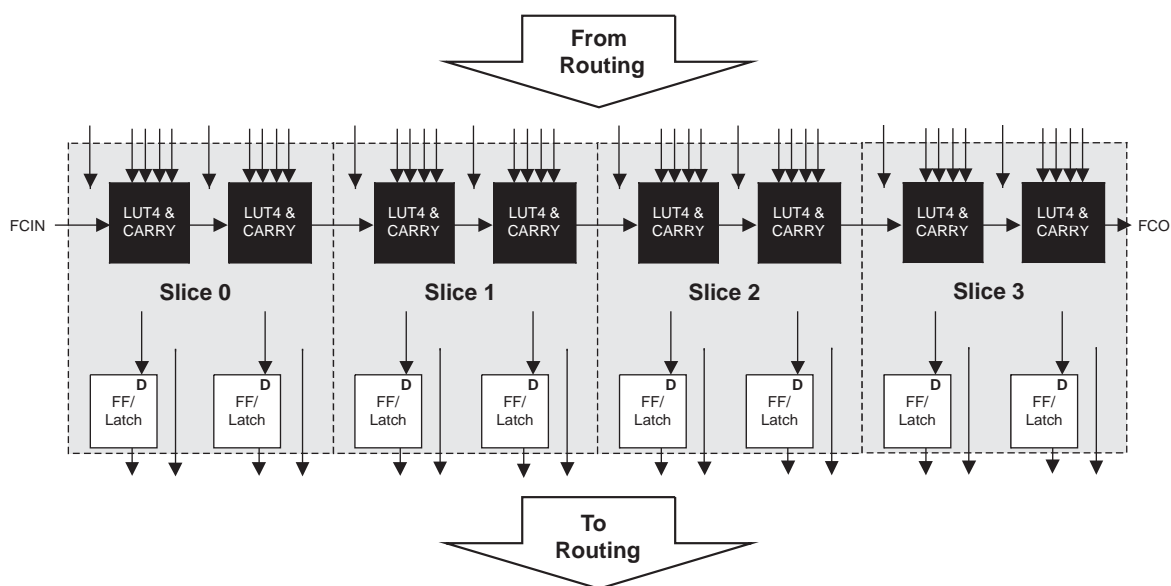
MachXO2 devices provide commonly used hardened functions such as SPI controller, I²C controller and timer/counter. MachXO2-640/U and higher density devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I²C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO2 devices are available for operation from 3.3 V, 2.5 V and 1.2 V power supplies, providing easy integration into the overall system.

PFU Blocks

The core of the MachXO2 device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.

Figure 2-3. PFU Block Diagram



Slices

Slices 0-3 contain two LUT4s feeding two registers. Slices 0-2 can be configured as distributed memory. Table 2-1 shows the capability of the slices in PFU blocks along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. The control logic performs set/reset functions (programmable as synchronous/ asynchronous), clock select, chip-select and wider RAM/ROM functions.

Table 2-1. Resources and Modes Available per Slice

Slice	PFU Block	
	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 1	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 2	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 3	2 LUT4s and 2 Registers	Logic, Ripple, ROM

Figure 2-4 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks. All slices have 15 inputs from routing and one from the carry-chain (from the adjacent slice or PFU). There are seven outputs: six for routing and one to carry-chain (to the adjacent PFU). Table 2-2 lists the signals associated with Slices 0-3.

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
 - A greater-than-or-equal-to B
 - A not-equal-to B
 - A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO2 devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO2 devices, please see TN1201, [Memory Usage Guide for MachXO2 Devices](#).

Table 2-3. Number of Slices Required For Implementing Distributed RAM

	SPR 16x4	PDPR 16x4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

Figure 2-8. sysMEM Memory Primitives

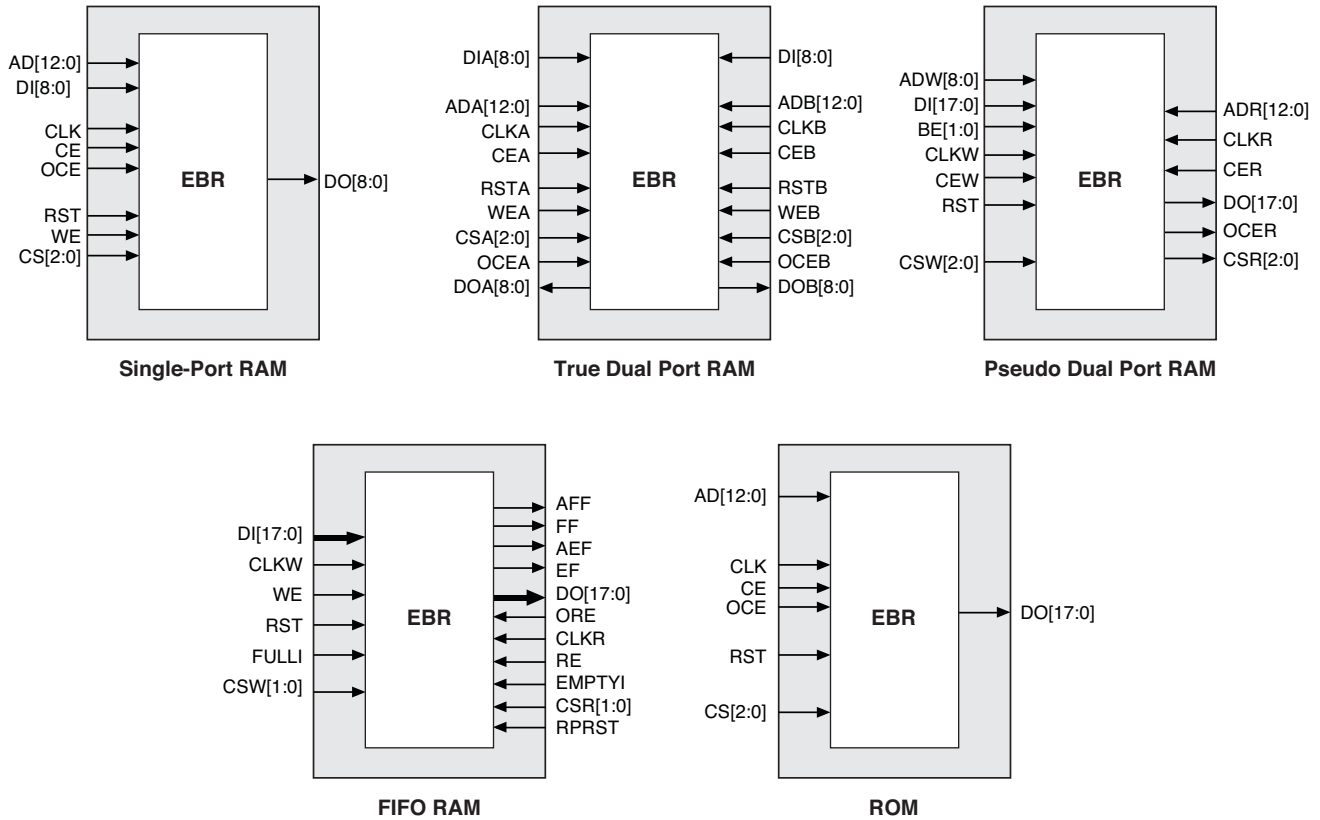


Table 2-6. EBR Signal Descriptions

Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE ¹	Output Clock Enable	Active High
RST	Reset	Active High
BE ¹	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	—
DO	Data Out	—
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	—
FF	FIFO RAM Full Flag	—
AEF	FIFO RAM Almost Empty Flag	—
EF	FIFO RAM Empty Flag	—
RPRST	FIFO RAM Read Pointer Reset	—

1. Optional signals.

2. For dual port EBR primitives a trailing 'A' or 'B' in the signal name specifies the EBR port A or port B respectively.

3. For FIFO RAM mode primitive, a trailing 'R' or 'W' in the signal name specifies the FIFO read port or write port respectively.

4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).

5. In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port chip select, ORE is the output read enable.

More information on the input gearbox is available in TN1203, [Implementing High-Speed Interfaces with MachXO2 Devices](#).

Output Gearbox

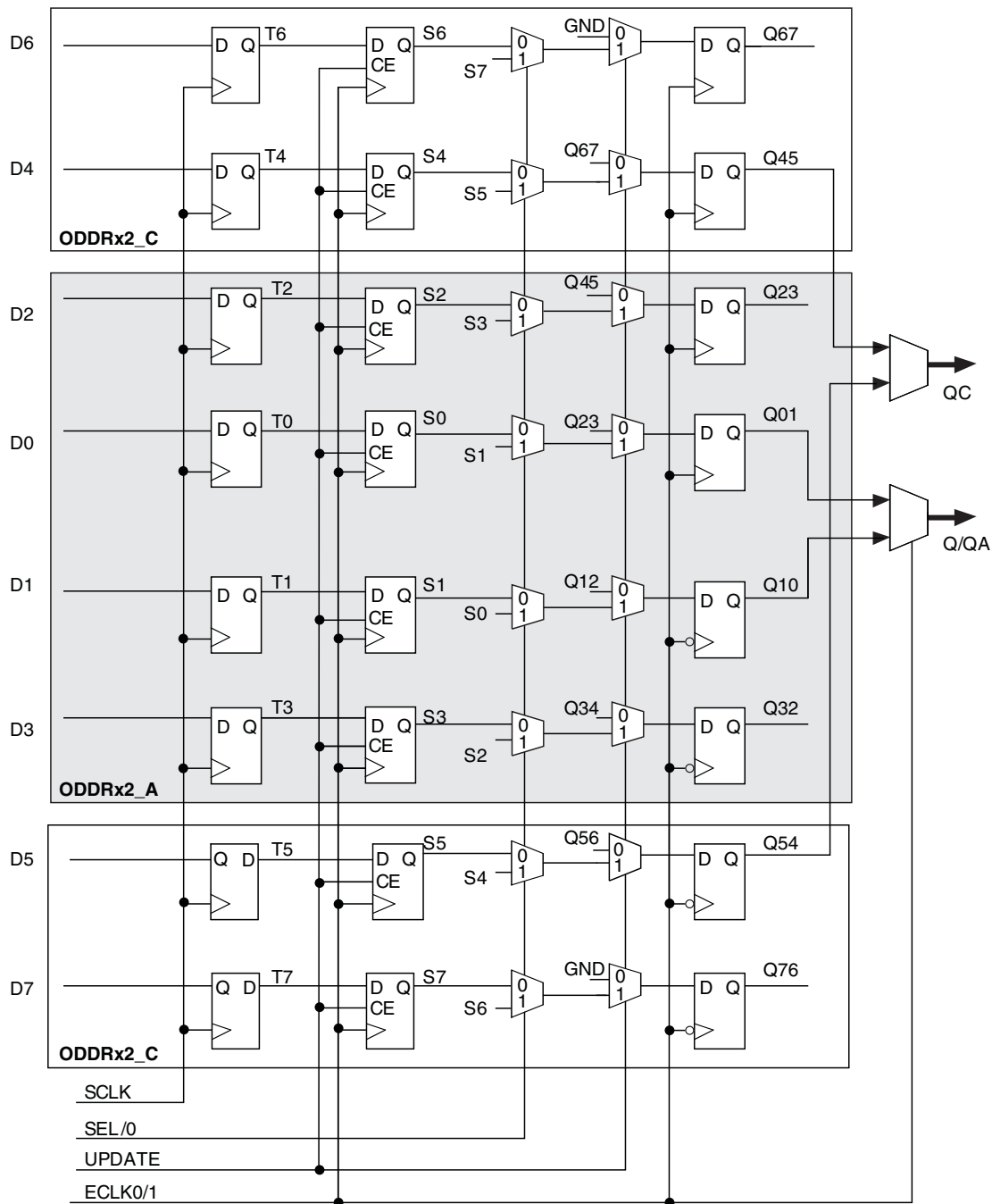
Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDR4 (8:1) gearbox or as two ODDR2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDR4(8:1): D[7:0]		
GDDR2(4:1)(IOL-A): D[3:0]		
GDDR2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-17 shows the output gearbox block diagram.

Figure 2-17. Output Gearbox



More information on the output gearbox is available in TN1203, [Implementing High-Speed Interfaces with MachXO2 Devices](#).

For more details on these embedded functions, please refer to TN1205, [Using User Flash Memory and Hardened Control Functions in MachXO2 Devices](#).

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I²C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, [Using User Flash Memory and Hardened Control Functions in MachXO2 Devices](#).

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC} .

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I²C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Static Supply Current – ZE Devices^{1, 2, 3, 6}

Symbol	Parameter	Device	Typ. ⁴	Units
I_{CC}	Core Power Supply	LCMXO2-256ZE	18	μA
		LCMXO2-640ZE	28	μA
		LCMXO2-1200ZE	56	μA
		LCMXO2-2000ZE	80	μA
		LCMXO2-4000ZE	124	μA
		LCMXO2-7000ZE	189	μA
I_{CCIO}	Bank Power Supply ⁵ $V_{CCIO} = 2.5 V$	All devices	1	μA

1. For further information on supply current, please refer to TN1198, [Power Estimation and Management for MachXO2 Devices](#).
2. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip oscillator is off, on-chip PLL is off. To estimate the impact of turning each of these items on, please refer to the following table or for more detail with your specific design use the Power Calculator tool.
3. Frequency = 0 MHz.
4. $T_J = 25^\circ C$, power supplies at nominal voltage.
5. Does not include pull-up/pull-down.
6. To determine the MachXO2 peak start-up current data, use the Power Calculator tool.

Static Power Consumption Contribution of Different Components – ZE Devices

The table below can be used for approximating static power consumption. For a more accurate power analysis for your design please use the Power Calculator tool.

Symbol	Parameter	Typ.	Units
I_{DCBG}	Bandgap DC power contribution	101	μA
I_{DCPOR}	POR DC power contribution	38	μA
$I_{DCIOBANKCONTROLLER}$	DC power contribution per I/O bank controller	143	μA

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max. ⁴ (mA)	I_{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVC MOS10R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO2 devices allow LVC MOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO2 devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO2 devices allow for LVC MOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1202, [MachXO2 sysIO Usage Guide](#).
3. The dual function I²C pins SCL and SDA are limited to a V_{IL} min of -0.25 V or to -0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of $n * 8$ mA. "n" is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

Input Standard	V_{CCIO} (V)	V_{IL} Max. (V)
LVC MOS 33	1.5	0.685
LVC MOS 25	1.5	0.687
LVC MOS 18	1.5	0.655

sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of MachXO2-640U, MachXO2-1200/U and higher density devices in the MachXO2 PLD family.

LVDS

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
V_{INP} V_{INM}	Input Voltage	$V_{CCIO} = 3.3$ V	0	—	2.605	V
		$V_{CCIO} = 2.5$ V	0	—	2.05	V
V_{THD}	Differential Input Threshold		±100	—		mV
V_{CM}	Input Common Mode Voltage	$V_{CCIO} = 3.3$ V	0.05	—	2.6	V
		$V_{CCIO} = 2.5$ V	0.05	—	2.0	V
I_{IN}	Input current	Power on	—	—	±10	μA
V_{OH}	Output high voltage for V_{OP} or V_{OM}	$R_T = 100$ Ohm	—	1.375	—	V
V_{OL}	Output low voltage for V_{OP} or V_{OM}	$R_T = 100$ Ohm	0.90	1.025	—	V
V_{OD}	Output voltage differential	$(V_{OP} - V_{OM})$, $R_T = 100$ Ohm	250	350	450	mV
ΔV_{OD}	Change in V_{OD} between high and low		—	—	50	mV
V_{OS}	Output voltage offset	$(V_{OP} + V_{OM})/2$, $R_T = 100$ Ohm	1.125	1.20	1.395	V
ΔV_{OS}	Change in V_{OS} between H and L		—	—	50	mV
I_{OSD}	Output short circuit current	$V_{OD} = 0$ V driver outputs shorted	—	—	24	mA

BLVDS

The MachXO2 family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

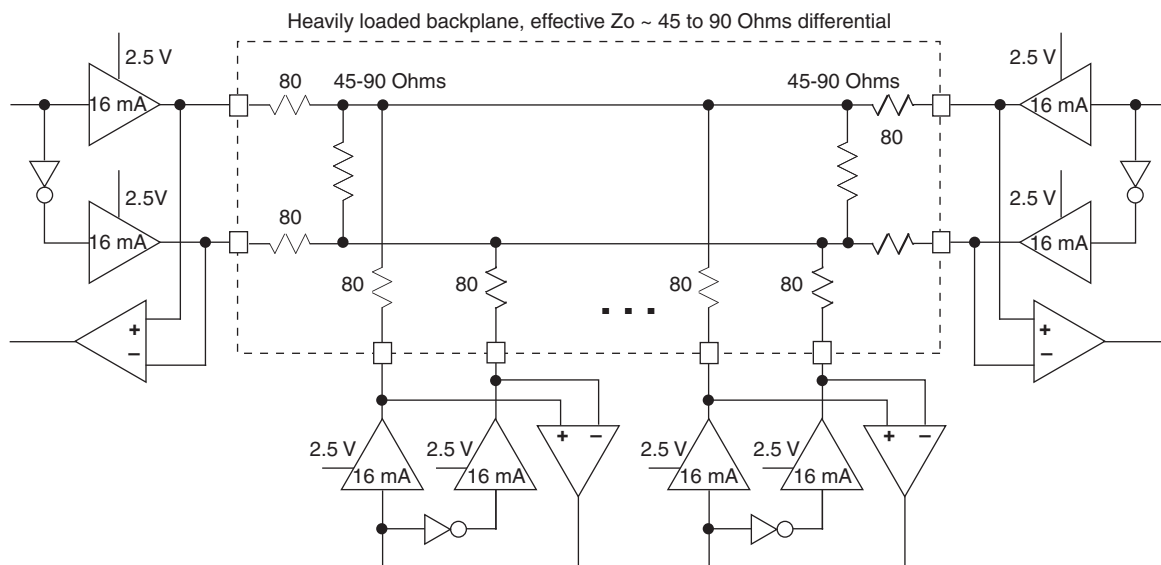


Table 3-2. BLVDS DC Conditions¹

Over Recommended Operating Conditions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
Z _{OUT}	Output impedance	20	20	Ohms
R _S	Driver series resistance	80	80	Ohms
R _{TLEFT}	Left end termination	45	90	Ohms
R _{TRIGHT}	Right end termination	45	90	Ohms
V _{OH}	Output high voltage	1.376	1.480	V
V _{OL}	Output low voltage	1.124	1.020	V
V _{OD}	Output differential voltage	0.253	0.459	V
V _{CM}	Output common mode voltage	1.250	1.250	V
I _{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.

Parameter	Description	Device	-3		-2		-1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR4_RX.ECLK.Centered ^{9, 12}									
t _{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only ¹¹	0.434	—	0.535	—	0.630	—	ns
t _{HO}	Input Data Hold After ECLK		0.385	—	0.395	—	0.463	—	ns
f _{DATA}	DDR4 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f _{DDR4}	DDR4 ECLK Frequency		—	210	—	176	—	146	MHz
f _{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
7:1 LVDS Inputs – GDDR71_RX.ECLK.7.1 ^{9, 12}									
t _{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only ¹¹	—	0.307	—	0.316	—	0.326	UI
t _{DVE}	Input Data Hold After ECLK		0.662	—	0.650	—	0.649	—	UI
f _{DATA}	DDR71 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f _{DDR71}	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f _{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDR1_TX.SCLK.Aligned ^{9, 12}									
t _{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides	—	0.850	—	0.910	—	0.970	ns
t _{DIB}	Output Data Invalid Before CLK Output		—	0.850	—	0.910	—	0.970	ns
f _{DATA}	DDR1 Output Data Speed		—	140	—	116	—	98	Mbps
f _{DDR1}	DDR1 SCLK frequency		—	70	—	58	—	49	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR1_TX.SCLK.Centered ^{9, 12}									
t _{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides	2.720	—	3.380	—	4.140	—	ns
t _{DVA}	Output Data Valid After CLK Output		2.720	—	3.380	—	4.140	—	ns
f _{DATA}	DDR1 Output Data Speed		—	140	—	116	—	98	Mbps
f _{DDR1}	DDR1 SCLK Frequency (minimum limited by PLL)		—	70	—	58	—	49	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDR2_TX.ECLK.Aligned ^{9, 12}									
t _{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t _{DIB}	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f _{DATA}	DDR2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f _{DDR2}	DDR2 ECLK frequency		—	140	—	117	—	97	MHz
f _{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz

Figure 3-5. Receiver RX.CLK.Aligned and MEM DDR Input Waveforms

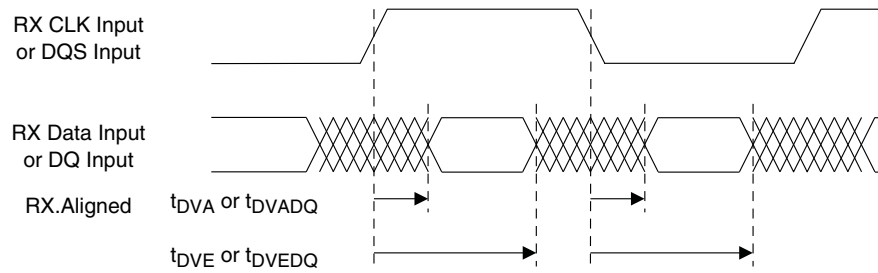


Figure 3-6. Receiver RX.CLK.Centered Waveforms

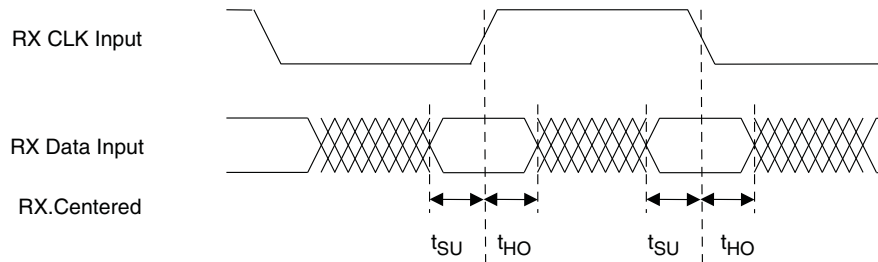


Figure 3-7. Transmitter TX.CLK.Aligned Waveforms

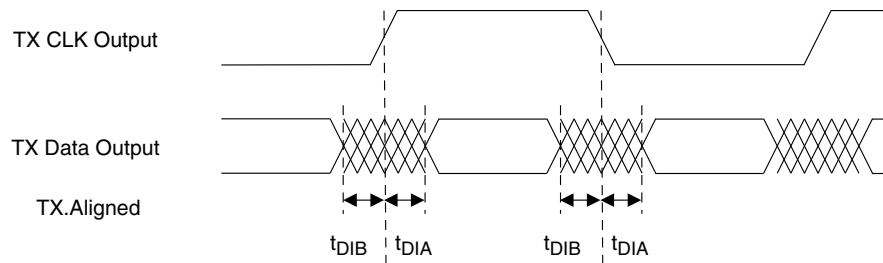


Figure 3-8. Transmitter TX.CLK.Centered and MEM DDR Output Waveforms

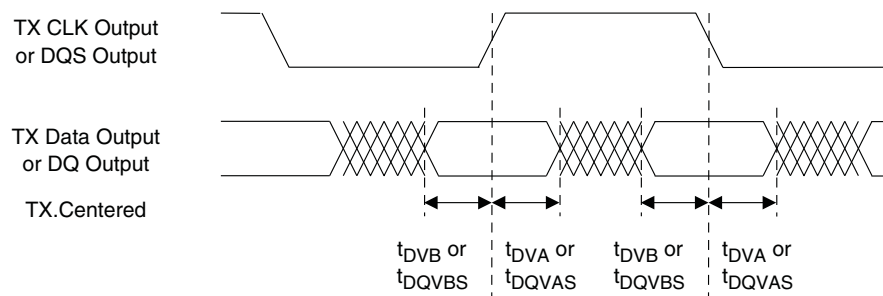


Figure 3-9. GDDR71 Video Timing Waveforms

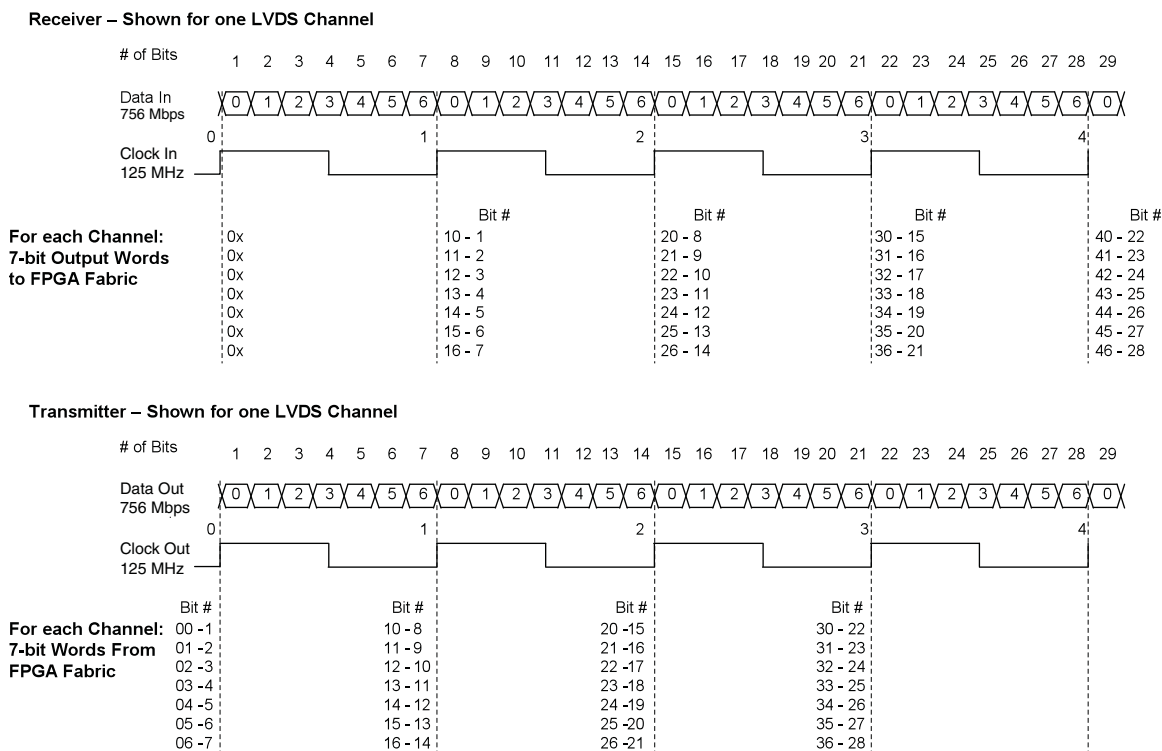


Figure 3-10. Receiver GDDR71_RX. Waveforms

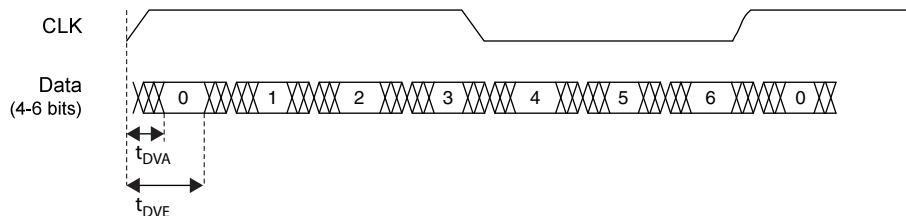
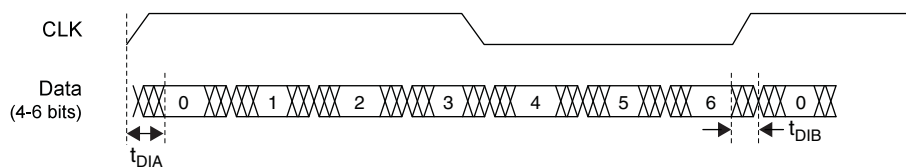


Figure 3-11. Transmitter GDDR71_TX. Waveforms



sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t _{PRGM}	PROGRAMN low pulse accept		55	—	ns
t _{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t _{INITL}	INITN low time	LCMXO2-256	—	30	μs
		LCMXO2-640	—	35	μs
		LCMXO2-640U/ LCMXO2-1200	—	55	μs
		LCMXO2-1200U/ LCMXO2-2000	—	70	μs
		LCMXO2-2000U/ LCMXO2-4000	—	105	μs
		LCMXO2-7000	—	130	μs
t _{DPPINIT}	PROGRAMN low to INITN low		—	150	ns
t _{DPPDONE}	PROGRAMN low to DONE low		—	150	ns
t _{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f _{MAX}	CCLK clock frequency		—	66	MHz
t _{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t _{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t _{STSU}	CCLK setup time		2	—	ns
t _{STH}	CCLK hold time		0	—	ns
t _{STCO}	CCLK falling edge to valid output		—	10	ns
t _{STOZ}	CCLK falling edge to valid disable		—	10	ns
t _{STOV}	CCLK falling edge to valid enable		—	10	ns
t _{SCS}	Chip select high time		25	—	ns
t _{SCSS}	Chip select setup time		3	—	ns
t _{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f _{MAX}	MCLK clock frequency		—	133	MHz
t _{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t _{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t _{STSU}	MCLK setup time		5	—	ns
t _{STH}	MCLK hold time		1	—	ns
t _{CSSPI}	INITN high to chip select low		100	200	ns
t _{MCLK}	INITN high to first MCLK edge		0.75	1	μs

Pinout Information Summary

	MachXO2-256					MachXO2-640			MachXO2-640U
	32 QFN ¹	48 QFN ³	64 ucBGA	100 TQFP	132 csBGA	48 QFN ³	100 TQFP	132 csBGA	144 TQFP
General Purpose I/O per Bank									
Bank 0	8	10	9	13	13	10	18	19	27
Bank 1	2	10	12	14	14	10	20	20	26
Bank 2	9	10	11	14	14	10	20	20	28
Bank 3	2	10	12	14	14	10	20	20	26
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Single Ended I/O	21	40	44	55	55	40	78	79	107
Differential I/O per Bank									
Bank 0	4	5	5	7	7	5	9	10	14
Bank 1	1	5	6	7	7	5	10	10	13
Bank 2	4	5	5	7	7	5	10	10	14
Bank 3	1	5	6	7	7	5	10	10	13
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Differential I/O	10	20	22	28	28	20	39	40	54
Dual Function I/O									
	22	25	27	29	29	25	29	29	33
High-speed Differential I/O									
Bank 0	0	0	0	0	0	0	0	0	7
Gearboxes									
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	0	0	0	0	0	0	0	0	7
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	0	0	0	0	0	0	0	0	7
DQS Groups									
Bank 1	0	0	0	0	0	0	0	0	2
VCCIO Pins									
Bank 0	2	2	2	2	2	2	2	2	3
Bank 1	1	1	2	2	2	1	2	2	3
Bank 2	2	2	2	2	2	2	2	2	3
Bank 3	1	1	2	2	2	1	2	2	3
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
VCC	2	2	2	2	2	2	2	2	4
GND ²	2	1	8	8	8	1	8	10	12
NC	0	0	1	26	58	0	3	32	8
Reserved for Configuration	1	1	1	1	1	1	1	1	1
Total Count of Bonded Pins	32	49	64	100	132	49	100	132	144

1. Lattice recommends soldering the central thermal pad onto the top PCB ground for improved thermal resistance.
2. For 48 QFN package, exposed die pad is the device ground.
3. 48-pin QFN information is 'Advanced'.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HC-4QN84I	4320	2.5 V / 3.3 V	–4	Halogen-Free QFN	84	IND
LCMXO2-4000HC-5QN84I	4320	2.5 V / 3.3 V	–5	Halogen-Free QFN	84	IND
LCMXO2-4000HC-6QN84I	4320	2.5 V / 3.3 V	–6	Halogen-Free QFN	84	IND
LCMXO2-4000HC-4TG144I	4320	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-4000HC-5TG144I	4320	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-4000HC-6TG144I	4320	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-4000HC-4MG132I	4320	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-4000HC-5MG132I	4320	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-4000HC-6MG132I	4320	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-4000HC-4BG256I	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-4000HC-5BG256I	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-4000HC-6BG256I	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-4000HC-4FTG256I	4320	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-4000HC-5FTG256I	4320	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-4000HC-6FTG256I	4320	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	IND
LCMXO2-4000HC-4BG332I	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	332	IND
LCMXO2-4000HC-5BG332I	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	332	IND
LCMXO2-4000HC-6BG332I	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	332	IND
LCMXO2-4000HC-4FG484I	4320	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-4000HC-5FG484I	4320	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-4000HC-6FG484I	4320	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HC-4TG144I	6864	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-7000HC-5TG144I	6864	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-7000HC-6TG144I	6864	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-7000HC-4BG256I	6864	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-7000HC-5BG256I	6864	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-7000HC-6BG256I	6864	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-7000HC-4FTG256I	6864	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-7000HC-5FTG256I	6864	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-7000HC-6FTG256I	6864	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	IND
LCMXO2-7000HC-4BG332I	6864	2.5 V / 3.3 V	–4	Halogen-Free caBGA	332	IND
LCMXO2-7000HC-5BG332I	6864	2.5 V / 3.3 V	–5	Halogen-Free caBGA	332	IND
LCMXO2-7000HC-6BG332I	6864	2.5 V / 3.3 V	–6	Halogen-Free caBGA	332	IND
LCMXO2-7000HC-4FG400I	6864	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	400	IND
LCMXO2-7000HC-5FG400I	6864	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	400	IND
LCMXO2-7000HC-6FG400I	6864	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	400	IND
LCMXO2-7000HC-4FG484I	6864	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-7000HC-5FG484I	6864	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-7000HC-6FG484I	6864	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	IND

For Further Information

A variety of technical notes for the MachXO2 family are available on the Lattice web site.

- TN1198, [Power Estimation and Management for MachXO2 Devices](#)
- TN1199, [MachXO2 sysCLOCK PLL Design and Usage Guide](#)
- TN1201, [Memory Usage Guide for MachXO2 Devices](#)
- TN1202, [MachXO2 sysIO Usage Guide](#)
- TN1203, [Implementing High-Speed Interfaces with MachXO2 Devices](#)
- TN1204, [MachXO2 Programming and Configuration Usage Guide](#)
- TN1205, [Using User Flash Memory and Hardened Control Functions in MachXO2 Devices](#)
- TN1206, [MachXO2 SRAM CRC Error Detection Usage Guide](#)
- TN1207, [Using TraceID in MachXO2 Devices](#)
- TN1074, [PCB Layout Recommendations for BGA Packages](#)
- TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#)
- AN8086, [Designing for Migration from MachXO2-1200-R1 to Standard \(non-R1\) Devices](#)
- AN8066, [Boundary Scan Testability with Lattice sysIO Capability](#)
- [MachXO2 Device Pinout Files](#)
- [Thermal Management](#) document
- [Lattice design tools](#)

For further information on interface standards, refer to the following web sites:

- JEDEC Standards (LVTTTL, LVCMOS, LVDS, DDR, DDR2, LPDDR): www.jedec.org
- PCI: www.pcisig.com

Date	Version	Section	Change Summary
January 2013	02.0	Introduction	Updated the total number IOs to include JTAGENB.
		Architecture	Supported Output Standards table – Added 3.3 V _{CCIO} (Typ.) to LVDS row.
			Changed SRAM CRC Error Detection to Soft Error Detection.
		DC and Switching Characteristics	Power Supply Ramp Rates table – Updated Units column for t _{RAMP} symbol.
			Added new Maximum sysIO Buffer Performance table.
			sysCLOCK PLL Timing table – Updated Min. column values for f _{IN} , f _{OUT} , f _{OUT2} and f _{PFD} parameters. Added t _{SPO} parameter. Updated footnote 6.
			MachXO2 Oscillator Output Frequency table – Updated symbol name for t _{STABLEOSC} .
			DC Electrical Characteristics table – Updated conditions for I _{IL} , I _{IH} symbols.
			Corrected parameters tDQVBS and tDQVAS
			Corrected MachXO2 ZE parameters tDVADQ and tDVEDQ
		Pinout Information	Included the MachXO2-4000HE 184 csBGA package.
		Ordering Information	Updated part number.
April 2012	01.9	Architecture	Removed references to TN1200.
		Ordering Information	Updated the Device Status portion of the MachXO2 Part Number Description to include the 50 parts per reel for the WLCSP package.
			Added new part number and footnote 2 for LCMXO2-1200ZE-1UWG25ITR50.
			Updated footnote 1 for LCMXO2-1200ZE-1UWG25ITR.
		Supplemental Information	Removed references to TN1200.
March 2012	01.8	Introduction	Added 32 QFN packaging information to Features bullets and MachXO2 Family Selection Guide table.
		DC and Switching Characteristics	Changed 'STANDBY' to 'USERSTDBY' in Standby Mode timing diagram.
		Pinout Information	Removed footnote from Pin Information Summary tables.
			Added 32 QFN package to Pin Information Summary table.
		Ordering Information	Updated Part Number Description and Ordering Information tables for 32 QFN package.
			Updated topside mark diagram in the Ordering Information section.

Date	Version	Section	Change Summary
May 2011	01.3	Multiple	Replaced “SED” with “SRAM CRC Error Detection” throughout the document.
		DC and Switching Characteristics	Added footnote 1 to Program Erase Specifications table.
		Pinout Information	Updated Pin Information Summary tables.
			Signal name SO/SISPISO changed to SO/SPISO in the Signal Descriptions table.
April 2011	01.2	—	Data sheet status changed from Advance to Preliminary.
		Introduction	Updated MachXO2 Family Selection Guide table.
		Architecture	Updated Supported Input Standards table.
			Updated sysMEM Memory Primitives diagram.
			Added differential SSTL and HSTL IO standards.
		DC and Switching Characteristics	Updates following parameters: POR voltage levels, DC electrical characteristics, static supply current for ZE/HE/HC devices, static power consumption contribution of different components – ZE devices, programming and erase Flash supply current.
			Added VREF specifications to sysIO recommended operating conditions.
			Updating timing information based on characterization.
			Added differential SSTL and HSTL IO standards.
		Ordering Information	Added Ordering Part Numbers for R1 devices, and devices in WLCSP packages.
			Added R1 device specifications.
January 2011	01.1	All	Included ultra-high I/O devices.
		DC and Switching Characteristics	Recommended Operating Conditions table – Added footnote 3.
			DC Electrical Characteristics table – Updated data for I_{IL} , I_{IH} , V_{HYST} typical values updated.
			Generic DDRX2 Outputs with Clock and Data Aligned at Pin (GDDR2_TX.ECLK.Aligned) Using PCLK Pin for Clock Input tables – Updated data for T_{DIA} and T_{DIB} .
			Generic DDRX4 Outputs with Clock and Data Aligned at Pin (GDDR4_TX.ECLK.Aligned) Using PCLK Pin for Clock Input tables – Updated data for T_{DIA} and T_{DIB} .
			Power-On-Reset Voltage Levels table - clarified note 3.
			Clarified VCCIO related recommended operating conditions specifications.
			Added power supply ramp rate requirements.
			Added Power Supply Ramp Rates table.
			Updated Programming/Erase Specifications table.
			Removed references to V_{CCP} .
		Pinout Information	Included number of 7:1 and 8:1 gearboxes (input and output) in the pin information summary tables.
			Removed references to V_{CCP} .
November 2010	01.0	—	Initial release.